Yixin

Advanced Power MOSFET SSS3N90A

FEATURES

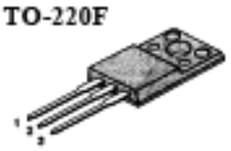
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 25 μA (Max.) @ V_{DS} = 900V
- Low $R_{DS(ON)}$: 4.679 Ω (Typ.)

BV_{DSS} = 900 V

$R_{DS(on)}$ = 6.2 Ω

I_D = 2 A

TO-220F



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current (T_C=25 °C)	2	A
	Continuous Drain Current (T_C=100 °C)	1.3	
I_{DM}	Drain Current-Pulsed ①	12	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy ②	286	mJ
I_{AR}	Avalanche Current ①	2	A
E_{AR}	Repetitive Avalanche Energy ①	3.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	1.5	V/ns
P_D	Total Power Dissipation (T_C=25 °C) Linear Derating Factor	35 0.28	W W/ °C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–	3.57	°C /W
$R_{\theta JA}$	Junction-to-Ambient	–	62.5	

Electrical Characteristics (T_C=25 ℃ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	900	--	--	V	V_{GS}=0V, I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	1.13	--	V/ ℃	I_D=250μA *See Fig 7*
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	3.5	V	V_{DS}=5V, I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=30V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-30V
I_{DSS}	Drain-to-Source Leakage Current	--	--	25	μA	V_{DS}=900V
		--	--	250		V_{DS}=720V, T_C=125 ℃
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	6.2	Ω	V_{GS}=10V, I_D=1A ④ *
g_{fs}	Forward Transconductance	--	1.78	--	Ω	V_{DS}=50V, I_D=1A ④
C_{iss}	Input Capacitance	--	590	770	pF	V_{GS}=0V, V_{DS}=25V, f =1MHz *See Fig 5*
C_{oss}	Output Capacitance	--	55	65		
C_{rss}	Reverse Transfer Capacitance	--	22	28		
$t_{d(on)}$	Turn-On Delay Time	--	16	40	ns	V_{DD}=450V, I_D=3A, R_G=16Ω *See Fig 13* ④ ⑤
t_r	Rise Time	--	26	60		
$t_{d(off)}$	Turn-Off Delay Time	--	47	105		
t_f	Fall Time	--	24	60		
Q_g	Total Gate Charge	--	28	37	nC	V_{DS}=720V, V_{GS}=10V, I_D=3A *See Fig 6 & Fig 12* ④ ⑤
Q_{gs}	Gate-Source Charge	--	5.5	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	11.9	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	2	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	12		
V_{SD}	Diode Forward Voltage ④	--	--	1.4	V	T_J=25℃, I_S=2A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	380	--	ns	T_J=25℃, I_F=3A, di_F/dt=100A/μs ④
Q_{rr}	Reverse Recovery Charge	--	1.9	--	μC	

Notes ;

Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
L=135mH, I_{AS}=2A, V_{DD}=50V, R_G=27Ω, Starting T_J=25 ℃
$I_{SD} \leq$ 3A, di/dt $\leq$90A/μs, $V_{DD} \leq BV_{DSS}$, Starting T_J=25 ℃
Pulse Test : Pulse Width = 250 μs, Duty Cycle $\leq$2%
Essentially independent of Operating Temperature

Fig 1. Output Characteristics

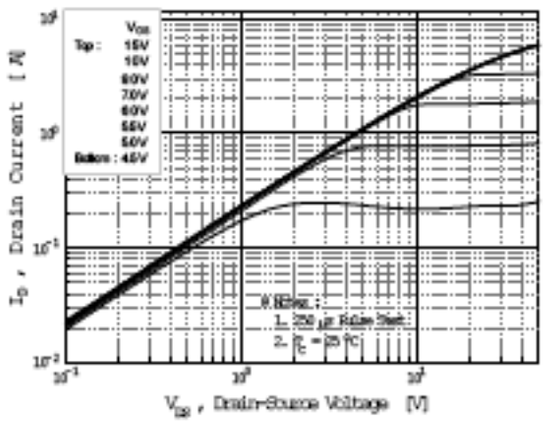


Fig 2. Transfer Characteristics

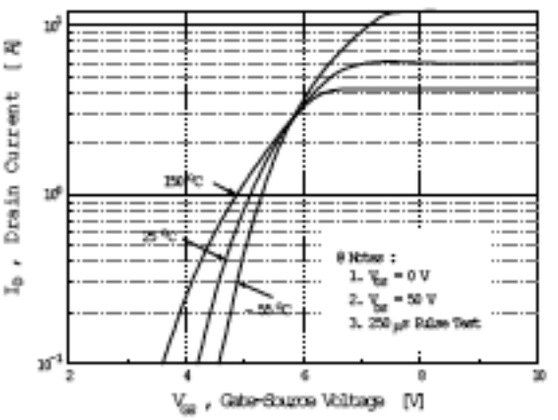


Fig 3. On-Resistance vs. Drain Current

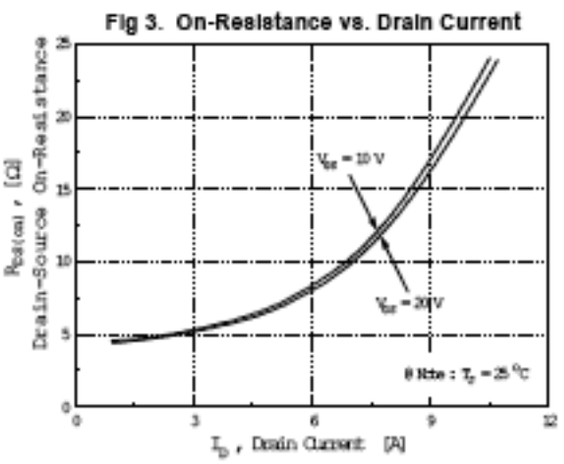


Fig 4. Source-Drain Diode Forward Voltage

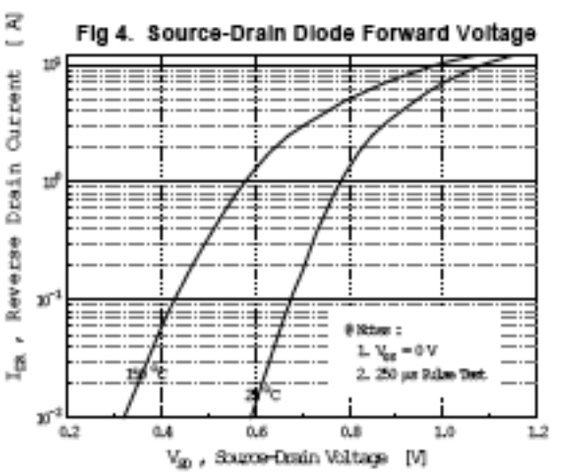


Fig 5. Capacitance vs. Drain-Source Voltage

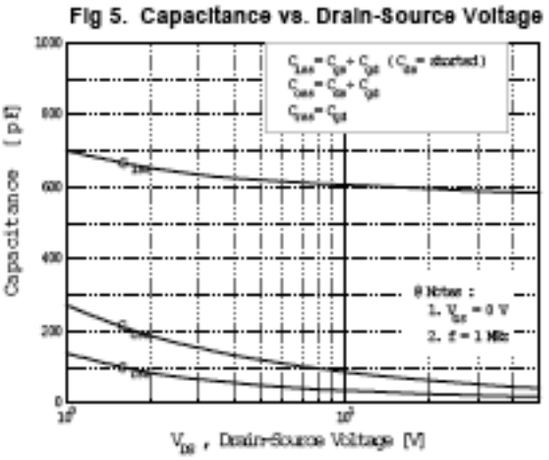


Fig 6. Gate Charge vs. Gate-Source Voltage